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A Single Pair of Weyl Fermions in Half-metallic EuCd₂As₂ Semimetal

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Abstract

Materials with the ideal case of a single pair of Weyl points (WPs) is highly desirable for elucidating the unique properties of Weyl fermions. $EuCd₂As₂$ is an anti-ferromagnetic topological insulator or Dirac semimetal depending on the different magnetic configurations. Using first-principles band structure calculations, we show that inducing ferromagnetism in $EuCd₂As₂$ can generate a single pair of WPs from splitting the single pair of anti-ferromagnetic Dirac points due to its half-metallic nature. Analysis with a low-energy effective Hamiltonian shows that a single pair of WPs is obtained in $EuCd₂As₂$ because the DPs are very close to the zone center and the ferromagnetic exchange splitting is large enough to push one pair of WPs to merge and annihilate at Γ while the other pair survives. Furthermore, we predict that alloying with Ba at the Eu site can stabilize the ferromagnetic configuration and generate a single pair of Weyl points without application of a magnetic field.

Introduction

Discoveries of symmetry-protected topological states in condensed matter physics and materials science have attracted great interest.¹⁻⁴ Among the different symmetries, time-reversal symmetry (TRS) Θ is key to understand many topological states, such as topological insulator (TI), because Θ is antiunitary for electrons and gives the degeneracy of Kramer pairs. Breaking TRS with magnetism can introduce other interesting topological states. For example, the quantum anomalous Hall effect (QAHE) has been realized in ferromagnetic TIs with magnetic dopants.⁵ AFM-TIs have also been proposed where an effective TRS can be defined by combining Θ and non-symmorphic translation $\tau_{1/2}$ (*S*= $\Theta \tau_{1/2}$). The preservation of *S* can lead to topological Z_2 classification even though Θ is broken. The surface states of an AFM-TI can either gap out or form a surface Dirac point (DP), depending on whether the surface orientation breaks or preserves S , with the former being proposed to host topological axion states⁷ with quantized magnetoelectric effects. Very recently, such an intrinsic AFM-TI has been reported in $MnBi₂Te₄.⁸⁻¹⁰$

 TRS is also a key factor in topological semimetals where broken TRS can lift the degeneracy of bulk DPs into Weyl points (WPs) of opposite chirality. Weyl points (WPs) were first proposed in TRS-broken systems, such as noncollinear antiferromagnetic (AFM) pyrochlore iridates¹¹, magnetically doped TI/normal insulator heterostructures¹², ferromagnetic (FM) $HgCr_2Se_4^{13}$ and strained $Hg_{1-x-y}Cd_xMn_yTe$ in a magnetic field¹⁴ before they were realized in compounds with broken inversion symmetry (IS) *P*, such as TaAs¹⁵⁻¹⁸ and WTe₂ families¹⁹⁻²³. However, bulk DPs can also exist in AFM systems, such as CuMnAs, due to the protection of the combined Θ*P*, although each of Θ and P by itself is broken.²⁴ Clearly, the interplay of magnetism, crystalline

symmetry, and topology provides a mechanism whereby magnetism can be used to control topological states.

For Weyl semimetals, a major challenge is to discover a material with the minimally possible, i.e., a single pair of WPs in the full Brillouin zone (BZ), which would greatly simplify the elucidation of their unique transport and optical properties, such as the universal form of anomalous Hall conductivity depending only on the distance between a single pair of WPs^{25} . $MnBi₂Te₄$ has recently been predicted to host a single pair of FM-WPs in the FM phase⁸. However, first-principles electronic structure calculations using experimentally determined lattice parameters found that the FM configuration of $MnBi₂Te₄$ is not semimetallic. The AFM-TI ground state of $MnBi₂Te₄$ has a band gap of 200 meV and the FM configuration is 46 meV/f.u. less stable. To form a pair of WPs in MnBi2Te4, the insulating gap needs to be closed by expanding the structure in the basal plane or under negative pressure. Given such requirements, it is not straightforward to realize the single pair of FM-WPs in semiconducting $MnBi₂Te₄$. In earlier studies, magnetically doped TI/normal insulator heterostructures¹² has been proposed to host a single pair of FM-WPs, but it has not been realized in real materials. Although a pair of FM-WPs with chirality of 2 has been predicted¹³ to exist in Chern semimetal HgCr₂Se₄ along the magnetization axis, there is an additional nodal loop protected by mirror symmetry at k_z =0 plane. The single pair of WPs has been proposed in strained $Hg_{1-x-y}Cd_xMn_yTe$ in a magnetic field by splitting the single DP at the Γ point¹⁴, but this DP can only exist at the phase boundary between TI and normal insulator transition, thus not stable. For the stable DPs protected by crystal symmetry, such as a pair of DPs along ΓA in BaAgBi²⁶, the splitting due to breaking TRS with Eu substitution results in two pairs of WPs, not a single pair. The pair of FM-WPs along

[110] axis in magnetic Heusler alloys²⁷ can be tuned to the Fermi energy (E_F) , but there are other sets of WPs between the valence and conduction bands.

 Thus, a FM semimetal hosting the ideal case of a single pair of WPs has not been found yet. A better starting place to search for such an ideal case is an AFM-DP semimetal or AFM-TI with a very small band gap.^{28, 29} EuCd₂As₂ is AFM with a Neel temperature of 9.5 K^{30, 31} and strong coupling is observed between transport and magnetism³². Resonant *x*-ray scattering measurements by Rahn *et al.*²⁹ have shown that the ground state magnetic structure of EuCd₂As₂ is an A-type AFM with moments aligned in the hexagonal layer. The A-type order with in-plane moments breaks the 3-fold rotational symmetry and an AFM-TI state with a band gap of 10 meV arises from the band inversion near the Γ point. A recent theoretical study by Hua *et al.*²⁸ found that if the AFM moment can be turned along c -axis in EuCd₂As₂ to restore the 3-fold rotational symmetry, then a single pair of AFM-DP can appear along ΓA and is protected by *SP* combination.28 Additionally, each of the AFM-DPs can be split into a pair of triply degenerated nodal points (TDNPs) when breaking *P*.

As shown in the calculation by Krishna *et al.*³³, the energy difference between AFM and FM is as small as \sim 2 meV/f.u, suggesting that the FM state is accessible under typical laboratory conditions. Rahn *et al*. 29 have shown that the saturation magnetic field to stabilize FM along *c* axis is about 1.5 T at 2 K. However, the topological properties of the FM configuration have not been studied yet. Here we use first-principles band structure calculations and discover that a FM configuration with moments along c axis of EuCd₂As₂ actually hosts a single pair of WPs, a unique feature due to half metallic nature of the system. Furthermore, we propose that alloying with Ba at the Eu site introduces an effective negative pressure that can stabilize FM over AFM. By introducing exchange splitting terms explicitly in a 4-band low-energy Hamiltonian for the

DPs, we find that a single pair of DPs will split into a single pair of WPs under the following conditions; (1) the DPs should be close to the BZ center and (2) the exchange splitting must be large enough to push two WPs from the opposite side of Γ point to merge and annihilate, while the other pair of WPs survive by being pushed away from the Γ point.

Computational Methods

All density functional theory^{34, 35} (DFT) calculations with and without spin-orbit coupling (SOC) were performed with the $PBE³⁶$ exchange-correlation functional using a plane-wave basis set and projector augmented wave 37 method, as implemented in the Vienna Ab-initio Simulation Package^{38, 39} (VASP). Using maximally localized Wannier functions⁴⁰⁻⁴², tight-binding models were constructed to reproduce closely the band structure including SOC within $\pm 1eV$ of the E_F with Eu *s-d-f*, Cd *s-p* and As *p* orbitals. The surface Fermi arcs and spectral functions were calculated with the surface Green's function methods^{$43-47$}. In the DFT calculations, we used a kinetic energy cutoff of 318 eV, Γ -centered Monkhorst-Pack⁴⁸ (11×11×3) *k*-point mesh, and a Gaussian smearing of 0.05 eV. To account for the strongly localized Eu 4*f* orbitals, an onsite U=5.0 eV is used^{28, 33}. For band structure calculations of EuCd₂As₂, the atomic basis positions and unit cell vectors are fixed to the experimental values³¹. To study the effect of alloying with Ba on the Eu site, a 20-atom supercell along *c* with alternating Ba and Ba/Eu layers (at 50% Ba substitution in every other layer) is fully relaxed in the FM and AFM configurations. The magnitude of force on each atom is reduced to below 0.01 eV/Å.

Results and Discussion

Figure 1 shows the bulk band structures and topological features of $EuCd₂As₂$ in different magnetic configurations. The crystal structure³¹ of EuCd₂As₂, with the primitive hexagonal unit cell of 5 atoms in space group 164 (*P*−*3m1*), is shown in Fig.1(b). The Eu atoms form a simple

hexagonal lattice at the 1*a* Wyckoff position. The As and Cd atoms at the 2*b* positions form the other four atomic layers with the sequence of -Cd-As-Eu-As-Cd- along the *c* axis. The As layer binds to Eu on one side and Cd on the other side. The structure has inversion symmetry, *P*. The Eu half-filled $4f$ shell hosts a large local magnetic moment. In EuCd₂As₂, the Eu moments prefer an intralayer FM coupling and an interlayer AFM coupling along *c* axis, i.e., an A-type AFM (AFMA), which requires doubling the unit cell along *c* direction. The insets of Fig.1(c) and (d) show two such magnetic configurations by singling out Eu atoms with magnetic moment directions along c (AFMAc) and along a (AFMAa), respectively. Because EuCd₂As₂ has a layered hexagonal lattice, the intralayer AFM will be frustrated and less stable than the AFMA configuration, which has been confirmed by the earlier DFT study²⁸. Our calculated magnetic moment of 6.99 μ_B on Eu site agrees with the earlier study²⁸. Experiment showed an effective moment of 7.88 μ_B and a saturated moment of 6.7 μ_B /Eu³¹.

Although magnetism breaks Θ , for the AFMA in EuCd₂As₂, Θ can be coupled with a lattice translation along *c*, giving the non-symmorphic TRS^{6, 28} *S*= $\Theta \tau_{1/2}$. For example, starting with either AFMA configurations in the inset of Fig.1(c) or (d), the magnetic moments are switched to the opposite direction under Θ and a translation $\tau_{1/2}$ along *c* returns the system to the starting configuration. The combination of *S* and *P* is antiunitary, $(SP)^2 = -1$, thus the bands at each general k-point are doubly degenerate for AFMA $EuCd₂As₂$ in the presence of SOC due to Kramer's theorem.

For EuCd₂As₂, different magnetic configurations affect the topological features of the system. Figure 1 presents the band structures of different magnetic configurations including the ground state AFMAa configuration found experimentally²⁹. Starting with the AFMAc band structure (Fig.1(a)), there is a sizable gap between valence and conduction bands along all the high-

symmetric directions except near Γ. The zoom in along ΓA in Fig.1(c) shows the band inversion between Cd *s* and As *p* derived orbitals near Γ. For AFMAc, the crossing is not gapped out due to the protection from the 3-fold rotational symmetry similar to a class- I^{49} DP in a non-magnetic system, resulting in a pair of AFM-DPs at $(0.0, 0.0, \pm 0.004 \text{ Å}^{-1})$. When the magnetic moments are oriented along *a* (Fig.1(d)) for AFMAa, the AFM-DPs are gapped out by breaking the 3-fold rotational symmetry and the system becomes an AFM-TI. Hua *et al*. 28 have also shown that the application of strain along the *a* axis is another way to break the 3-fold rotational symmetry and open up a band gap in the AFMAc phase. The AFM-TI has a special gapped surface state if the open boundary is along *c,* resulting in half-integer quantum Hall effect and axion states. In summary, our DFT+U+SOC calculations and analysis agree with earlier studies^{29, 33} for $EuCd₂As₂$ on the topological features of the AFMA states.

If the AFMAa ground state can be switched into a FMc configuration, then *S* will be broken and the double degeneracy will be lifted. Rahn *et al*. 29 have shown that the saturation magnetic field to stabilize FM along *c* axis is about 1.5 T at 2 K. In Fig.1(e), we show that yet another interesting topological feature, a single pair of WPs, will emerge in the FMc state. This is a unique feature due to the half-metallic nature of the system (see below). The Berry curvature calculation in Fig.1(f) indeed shows the source and sink for this single pair of WPs at (0.0, 0.0, ± 0.03 1/Å) on either side of the Γ point. Note that the distance between FM-WPs is increased compared to AFM-DPs because the band crossing is pushed away from Γ.

When projected onto the crystalline (001) surface of EuCd₂As₂, the WPs of opposite chirality overlap in the FMc state, thus there will be no open Fermi arcs. In contrast, the single pair of WPs do not overlap when projected on (110) surface and open Fermi arcs connecting the projected WPs are expected. Figure 2 shows such open Fermi arcs on both the top and bottom (110) surfaces of EuCd₂As₂ with Cd termination. In Fig.2(a) and (b) the Fermi arcs connect two hole pockets right at E_F , each on the opposite (110) surface. At higher energies, the hole pockets shrink and eventually reach the energy of the WPs at E_F+48 meV where the size of the Fermi arcs is maximal, spanning 0.06 1/Å. This situation corresponds to the ideal case of two open Fermi arcs connecting a single pair of WPs in the full BZ, each on the opposite surface, which has only been described schematically and without confirmation in any material system. Here we predict that such an ideal case of a single pair of WPs can be realized in FM $EuCd₂As₂$.

Normally, we expect that one pair of DPs will split into two pairs of WPs when breaking Θ or, in our case, *S*. Where does the other pair of WPs go in $EuCd₂As₂$? To clarify why and how a single pair of FM-WPs can arise from a single pair of AFM-DPs in $EuCd₂As₂$ upon breaking *S*, we present the evolution of band structures along ΓA direction in Fig.3 for different magnetic configurations. First, we turn off the magnetism in $EuCd₂As₂$ by treating the Eu 4*f* orbitals as core electrons. The system retains both Θ and *P* symmetries. The non-magnetic band structure without SOC is shown in Fig.3(a). It is a semiconductor with a band gap of 200 meV. The valence band has orbital degeneracy of As p_x and p_y , thus is 4-fold degenerated when spin is included. The conduction band is derived from Cd *s* orbital and has 2-fold degeneracy from spin. Turning on SOC in Fig.3(b), the orbital degeneracy between As p_x and p_y is lifted, but still maintains 2-fold degeneracy from spin because of Θ and *P*. The band gap is reduced to 100 meV.

For AFMA with 4*f* moment on Eu atoms and the unit cell doubled along *c* axis, Θ is broken, but *S* is not broken. The combination of *S* and *P* still gives 2-fold degeneracy for a general *k*point. Comparing Fig.3(c) to Fig.3(a) (without SOC) and Fig.3(d) to Fig.3(b) (with SOC), the main effect of AFMAc order is a band folding due to doubling of the unit cell along *c*. Without

SOC in Fig.3(c), the valence band has 4-fold degeneracy from both the spin and orbital degeneracy (As *px* and *py*), while the conduction band derived from Cd *s* orbital only has 2-fold spin degeneracy. The orbital degeneracy for the valence band can be clearly seen in the colorcoding of the folded branch from -0.7 at Γ to -0.5 eV at A, which has the opposite dispersion to the valence band. The lower branch of the valence band crosses another band mostly of As *pz* (Eu *f*) character near Γ (A). The conduction band has flat folded branch with Cd *s* character and the higher energy conduction band is mostly of Cd s , p_z and As p_z character. Each of these three conduction bands has 2-fold spin degeneracy.

Without SOC, the AFMA valence and conduction bands still do not cross, and a small band gap remains at Γ. When SOC is turned on in Fig.3(d), the orbital degeneracy of As *px* and *py* valence bands are lifted. Because of SOC, now *j* is good quantum number. The valence band with a total angular momentum of $J=3/2$ is split into two, one with $j_z=\pm 3/2$ and the other $j_z=\pm 1/2$; each is 2-fold degenerate due to *S* and *P*. The *J*=1/2 conduction band is also 2-fold degenerate. Importantly, SOC induces a band inversion around Γ between the valence $\left|\frac{3}{2}, \pm \frac{1}{2}\right|$ and conduction $\left|\frac{1}{2}, \pm \frac{1}{2}\right|$. The system becomes a topological semimetal with a single pair of AFM-DPs, as discussed by Hua *et al*. 28

We now consider the case for FM order, where *S* is broken and the 2-fold spin degeneracy is lifted. Without SOC, comparing Fig.3(e) to Fig.3(a), there is a large exchange splitting effect, giving two sets of bands, spin up and down. This results in a unique half-metallic feature where only the spin-up valence and conduction bands cross each other at *EF*, while the spin-down bands do not cross and maintain a gap. This crossing between the spin-up valence and conduction bands is a TDNP because the valence band has the 2-fold orbital degeneracy between As p_x and p_y . When SOC is turned on for the FMc configuration in Fig.3(f), both the orbital and spin degeneracies are fully lifted, and the 4-fold degenerate valence band in Fig.1(a) now becomes four individual bands. The spin and orbital degeneracies of other bands (including the conduction band) are already fully lifted by the broken *S* in the FM state. The crossing of half-metallic spinup valence and conduction bands near Γ is preserved with SOC. Importantly, the degeneracy of this crossing is reduced from three for TDNP to two, thus generating a WP.

The connection between the AFM-DPs $(Fig.3(d))$ and the FM-WPs $(Fig.3(f))$ can be understood by unfolding the bands and then lifting the spin degeneracy due to the breakdown of $(SP)^2$ =−1. The usual scenario of a single DP splitting into two WPs does not work here because of the half-metallicity. Or equivalently, the WP closer to Γ can merge with another WP of the opposite chirality from the other side of Γ and annihilate to form a gap.

To get a more generic picture of splitting a single pair of DPs into a single pair of WPs in a half-metal, we introduce the relevant low-energy Hamiltonian. We start with the 4-band *k.p* model for AFM-DP in EuCd₂As₂ with $\left|\frac{1}{2},+\frac{1}{2}\right\rangle$, $\left|\frac{3}{2},+\frac{3}{2}\right\rangle$, $\left|\frac{1}{2},-\frac{1}{2}\right\rangle$ $\frac{1}{2}$ and $\left|\frac{3}{2}, -\frac{3}{2}\right|$ $\frac{3}{2}$ in that order. This is similar to class-I DP in Na₃Bi⁵⁰ and Cd₃As₂⁵¹, except that the off-diagonal matrix elements are in the k_{\pm} order. We can add the FM exchange splitting as two terms, one is orbital dependent $h_1 \sigma_z \otimes \tau_z$ and the other spin dependent $h_2 \sigma_z \otimes I$, where h_1 and h_2 are exchange splitting parameters, σ and τ are the Pauli matrices for spin and orbital, respectively, and *I* is the identity matrix. Then the total Hamiltonian is

$$
H_{eff}(k) =
$$
\n
$$
\varepsilon_{0}(k) + \begin{pmatrix} M(k) + h_{1} + h_{2} & Ak_{+} & 0 & Bk_{+} \\ Ak_{-} & -M(k) - h_{1} + h_{2} & Bk_{+} & 0 \\ 0 & Bk_{-} & M(k) + h_{1} - h_{2} & -Ak_{-} \\ Bk_{-} & 0 & -Ak_{+} & -M(k) - h_{1} - h_{2} \end{pmatrix}
$$
\n
$$
(1)
$$

where $k_{\pm} = k_x \pm ik_y$, $M(k) = M_0 - M_1k_z^2 - M_2(k_x^2 + k_y^2)$ and $\varepsilon_0(k) = C_0 + C_1k_z^2 +$ $C_2(k_x^2 + k_y^2)$. After diagonalization, the solutions for the eigenvalues are

$$
E(k) = \varepsilon_0(k) \pm \sqrt{(M(k) + sgn h_1)^2 + (A^2 + B^2)(k_x^2 + k_y^2)} + sgn h_2
$$
 (2)

where *sgn* takes on \pm independently from the one before the square root. When fitted to DFT calculated band structures of EuCd₂As₂, the following parameters are obtained, C_0 =–0.0005 eV, C_1 =47.8237 eVÅ², C_2 =55.0803 eVÅ², M₀=-0.0039 eV, M₁=-54.5293 eVÅ², M₂=1.6425 eVÅ² and $\tilde{A} = 2.6902 \text{ eV} \text{Å}$ for $\tilde{A}^2 = A^2 + B^2$.

In Fig.4, we plot the bands from the low-energy effective Hamiltonian (Eqn.(2)) with different values of h_1 and h_2 . When $h_1 = h_2 = 0$ in Fig.4(a), we have a 4-fold degenerate AFM-DP due to the combined *SP*. When *S* is broken with $h_1 = 3.0$ meV and $h_2 = 0$ in Fig.4(b), a pair of FM-WPs split from the AFM-DPs. By increasing h_2 such that $h_1 = h_2 = 3.0$ meV in Fig.4(c), two TDNPs are produced because the valence band is 2-fold degenerate, but not the conduction band. Increasing h_1 to 6.0 meV in Fig.4(d) is enough to create a gap between one pair of valence and conduction bands. In effect, one of the two WPs pairs on opposite sides of Γ meet and annihilate, while the other pair of WPs is pushed further away from Γ. This can happen in $EuCd₂As₂$ is because AFM-DPs are very close to Γ at ± 0.004 (1/Å), comparing to ± 0.084 and ± 0.032 (1/Å) in $\text{Na}_3\text{Bi}^{50}$ and $\text{Cd}_3\text{As}_2^{51}$, respectively.

Although the FM configuration of $EuCd₂As₂$ hosts the desirable single pair of WPs, experiment has shown that the ground state of $EuCd₂As₂$ is AFMA with magnetic moments lying in-plane. To stabilize FM vs. AFMA, one can apply a saturation magnetic field of about 1.5 T along the *c* axis at 2 K as shown by Rahn *et al.*²⁹ Due to the small difference in energy between AFMA and FM states, another possibility is to stabilize the FM state by expanding the lattice using strain or by the application of an effective negative pressure by alloying. For example, in the same crystal structure, the lattice constants of $BaCd₂As₂$ are \sim 5% larger than EuCd₂As₂. As a proof of principle, we have constructed a 20-atom supercell along *c* with an alternating Ba and Eu layers (i.e. with equal concentrations of Ba and Eu). For pure $EuCd₂As₂$, the DFT+U+SOC relaxed lattice constants of $a=4.49$ Å and $c=7.38$ Å agree very well with experimental data³¹ of $a=4.4499$ Å and $c=7.35$ Å (within 1%). For EuBaCd₄As₄, the lattice constants increase to $a=4.53$ Å and *c*=7.56 Å, and FMc is 0.25 meV/f.u. more stable than AFMAc. Figure 5 shows the band structures of EuBaCd4As4 along ΓA for the AFMAc and FMc configurations. The single pair of DPs for AFMAc in Fig.5(a) and single pair of WPs for FM in Fig.5(b) are retained. The Baderived bands do not affect the half-metallic feature and the crossings between As *p* and Cd *s* derived bands near the *EF*. The increased lattice constants obtained from alloying with Ba at the Eu site result in a ground state FMc configuration with a single pair of WPs. To prove that the proposed EuBaCd4As4 is thermally stable, we have also calculated the phonon dispersion in a $(2\times2\times2)$ supercell as shown in Fig.6. Indeed, there are no negative phonon modes and the structure is thermally stable.

Conclusion

In conclusion, first-principles band structure calculations show that $EuCd₂As₂$ in a ferromagnetic configuration can host an ideal case of a single pair of Weyl points due to the halfmetallic nature of the system. Analysis with a low-energy effective Hamiltonian shows that this ideal case is obtained in $EuCd₂As₂ because the Dirac points in the AFMA state are very close to$ the zone center and the ferromagnetic exchange splitting is large enough to push one pair of WPs, one from each side of Γ, to merge and annihilate. Furthermore, we have shown that by alloying with Ba at the Eu site, the ferromagnetic configuration can become the ground state. $EuCd₂As₂$ thin films grown with molecular beam epitaxy along a (110) surface and stabilized into the FM state with strain engineering or Ba alloying will be desirable systems to investigate such an ideal case of a single pair of Weyl points.

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Note added: Recently, we learned a similar work on EuCd₂As₂ by Soh *et al.*⁵²

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Figure 1. (a) Band structure of $EuCd₂As₂$ in PBE+U+SOC for A-type AFM with magnetic moment along *c* axis (AFMAc). (b) crystal structure of EuCd₂As₂ in space group 164 (*P*−*3m1*). Band structure along ΓA for (c) AFMAc, (d) moments in-plane along major axis (AFMAa) breaking 3-fold rotational symmetry, and (e) FM moment along c (FMc) breaking the combined *S*=Θτ*1/2* symmetry. The green shade over the band structure stands for the projection of As *p*

orbitals. (f) Berry curvature on the *kx*-*kz* plane showing chirality for the single pair of Weyl points in (e).

Figure 2. Fermi arcs at E_F on the (a) top and (b) bottom (110) surfaces of EuCd₂As₂ in FMc with a single pair of Weyl points; and those at $E_F+0.048$ eV on the (c) top and (d) bottom (110) surfaces. The color scheme of the intensity from high to low is red, white and blue.

Figure 3. Bulk band structure of EuCd₂As₂ along ΓA direction for non-magnetic (NM) without Eu 4f in (a) PBE and (b) PBE+SOC; AFM in (c) PBE+U and (d) PBE+U+SOC; and FM in (e) PBE+U and (f) PBE+U+SOC. The NM and FM have the primitive 5-atom unit cell. The AFM has the 10-atom unit cell by doubling along *c* direction. The green shade shows the projection on

Figure 4. Band structure near Γ along ΓA of the 4-band low-energy Hamiltonian based on EuCd₂As₂ with different values of exchange splitting parameters h_1 and h_2 in meV.

Figure 5. Band structure of 50% Ba (gray) substituted $EuCd₂As₂$, or $EuBaCd₄As₄$, for (a) AFMAc and (b) FMc with moment along *c*. Unit cells are fully relaxed and FMc is preferred. The green shade shows the projection on As *p* orbitals.

Figure 6. Phonon dispersion of EuBaCd₄As₄ calculated in a $(2\times2\times2)$ supercell of the FM configuration.

References

- 1. M. Z. Hasan, C. L. Kane, Colloquium: Topological insulators. *Rev Mod Phys* **82**, 3045 (2010).
- 2. X.-L. Qi, S.-C. Zhang, Topological insulators and superconductors. *Rev Mod Phys* **83**, 1057-1110 (2011).
- 3. C. K. Chiu, J. C. Y. Teo, A. P. Schnyder, S. Ryu, Classification of topological quantum matter with symmetries. *Rev Mod Phys* **88**, 035005 (2016).
- 4. N. P. Armitage, E. J. Mele, A. Vishwanath, Weyl and Dirac semimetals in threedimensional solids. *Rev Mod Phys* **90**, 015001 (2018).
- 5. C. Z. Chang, J. S. Zhang, X. Feng, J. Shen, Z. C. Zhang, M. H. Guo, K. Li, Y. B. Ou, P. Wei, L. L. Wang, Z. Q. Ji, Y. Feng, S. H. Ji, X. Chen, J. F. Jia, X. Dai, Z. Fang, S. C. Zhang, K. He, Y. Y. Wang, L. Lu, X. C. Ma, Q. K. Xue, Experimental Observation of the Quantum Anomalous Hall Effect in a Magnetic Topological Insulator. *Science* **340**, 167- 170 (2013).
- 6. R. S. K. Mong, A. M. Essin, J. E. Moore, Antiferromagnetic topological insulators. *Phys Rev B* **81**, 245209 (2010).
- 7. A. M. Essin, J. E. Moore, D. Vanderbilt, Magnetoelectric Polarizability and Axion Electrodynamics in Crystalline Insulators (vol 102, 146805, 2009). *Phys Rev Lett* **103**, 146805 (2009).
- 8. D. Zhang, M. Shi, T. Zhu, D. Xing, H. Zhang, J. Wang, Topological axion states in magnetic insulator MnBi\$ 2\$Te\$ 4\$ with the quantized magnetoelectric effect. arXiv:1808.08014 (2018).
- 9. Y. Gong, J. Guo, J. Li, K. Zhu, M. Liao, X. Liu, Q. Zhang, L. Gu, L. Tang, X. Feng, D. Zhang, W. Li, C. Song, L. Wang, P. Yu, X. Chen, Y. Wang, H. Yao, W. Duan, Y. Xu, S.- C. Zhang, X. Ma, Q.-K. Xue, K. He, Experimental realization of an intrinsic magnetic topological insulator. arXiv:1809.07926 (2018).
- 10. M. M. Otrokov, I. I. Klimovskikh, H. Bentmann, A. Zeugner, Z. S. Aliev, S. Gass, A. U. B. Wolter, A. V. Koroleva, D. Estyunin, A. M. Shikin, M. Blanco-Rey, M. Hoffmann, A. Y. Vyazovskaya, S. V. Eremeev, Y. M. Koroteev, I. R. Amiraslanov, M. B. Babanly, N. T. Mamedov, N. A. Abdullayev, V. N. Zverev, B. Büchner, E. F. Schwier, S. Kumar, A. Kimura, L. Petaccia, G. Di Santo, R. C. Vidal, S. Schatz, K. Kißner, C.-H. Min, S. K. Moser, T. R. F. Peixoto, F. Reinert, A. Ernst, P. M. Echenique, A. Isaeva, E. V. Chulkov, Prediction and observation of the first antiferromagnetic topological insulator. arXiv:1809.07389 (2018).
- 11. X. G. Wan, A. M. Turner, A. Vishwanath, S. Y. Savrasov, Topological semimetal and Fermi-arc surface states in the electronic structure of pyrochlore iridates. *Phys Rev B* **83**, 205101 (2011).
- 12. A. A. Burkov, L. Balents, Weyl Semimetal in a Topological Insulator Multilayer. *Phys Rev Lett* **107**, 127205 (2011).
- 13. G. Xu, H. M. Weng, Z. J. Wang, X. Dai, Z. Fang, Chern Semimetal and the Quantized Anomalous Hall Effect in HgCr2Se4. *Phys Rev Lett* **107**, 186806 (2011).
- 14. D. Bulmash, C. X. Liu, X. L. Qi, Prediction of a Weyl semimetal in Hg1-x-yCdxMnyTe. *Phys Rev B* **89**, 081106(R) (2014).
- 15. S. Y. Xu, I. Belopolski, N. Alidoust, M. Neupane, G. Bian, C. L. Zhang, R. Sankar, G. Q. Chang, Z. J. Yuan, C. C. Lee, S. M. Huang, H. Zheng, J. Ma, D. S. Sanchez, B. K. Wang, A. Bansil, F. C. Chou, P. P. Shibayev, H. Lin, S. Jia, M. Z. Hasan, Discovery of a Weyl fermion semimetal and topological Fermi arcs. *Science* **349**, 613-617 (2015).
- 16. B. Q. Lv, H. M. Weng, B. B. Fu, X. P. Wang, H. Miao, J. Ma, P. Richard, X. C. Huang, L. X. Zhao, G. F. Chen, Z. Fang, X. Dai, T. Qian, H. Ding, Experimental Discovery of Weyl Semimetal TaAs. *Phys Rev X* **5**, 031013 (2015).
- 17. H. M. Weng, C. Fang, Z. Fang, B. A. Bernevig, X. Dai, Weyl Semimetal Phase in Noncentrosymmetric Transition-Metal Monophosphides. *Phys Rev X* **5**, 011029 (2015).
- 18. S. M. Huang, S. Y. Xu, I. Belopolski, C. C. Lee, G. Q. Chang, B. K. Wang, N. Alidoust, G. Bian, M. Neupane, C. L. Zhang, S. Jia, A. Bansil, H. Lin, M. Z. Hasan, A Weyl Fermion semimetal with surface Fermi arcs in the transition metal monopnictide TaAs class. *Nat Commun* **6**, 7373 (2015).
- 19. L. N. Huang, T. M. McCormick, M. Ochi, Z. Zhao, M. Suzuki, R. Arita, Y. Wu, D. X. Mou, H. Cao, J. Yan, N. Trivedi, A. Kaminski, Spectroscopic evidence for a type II Weyl semimetallic state in MoTe2. *Nat Mater* **15**, 1155-1160 (2016).
- 20. A. A. Soluyanov, D. Gresch, Z. J. Wang, Q. S. Wu, M. Troyer, X. Dai, B. A. Bernevig, Type-II Weyl semimetals. *Nature* **527**, 495-498 (2015).
- 21. Y. Wu, N. H. Jo, M. Ochi, L. Huang, D. X. Mou, S. L. Bud'ko, P. C. Canfield, N. Trivedi, R. Arita, A. Kaminski, Temperature-Induced Lifshitz Transition in WTe2. *Phys Rev Lett* **115**, 166602 (2015).
- 22. I. Belopolski, S. Y. Xu, Y. Ishida, X. C. Pan, P. Yu, D. S. Sanchez, H. Zheng, M. Neupane, N. Alidoust, G. Q. Chang, T. R. Chang, Y. Wu, G. Bian, S. M. Huang, C. C. Lee, D. X. Mou, L. N. Huang, Y. Song, B. G. Wang, G. H. Wang, Y. W. Yeh, N. Yao, J. E. Rault, P. Le Fevre, F. Bertran, H. T. Jeng, T. Kondo, A. Kaminski, H. Lin, Z. Liu, F. Q. Song, S. Shin, M. Z. Hasan, Fermi arc electronic structure and Chern numbers in the type-II Weyl semimetal candidate MoxW1-xTe2. *Phys Rev B* **94**, 085127 (2016).
- 23. Y. Wu, D. X. Mou, N. H. Jo, K. W. Sun, L. N. Huang, S. L. Bud'ko, P. C. Canfield, A. Kaminski, Observation of Fermi arcs in the type-II Weyl semimetal candidate WTe2. *Phys Rev B* **94**, 121113(R) (2016).
- 24. P. Z. Tang, Q. Zhou, G. Xu, S. C. Zhang, Dirac fermions in an antiferromagnetic semimetal. *Nat Phys* **12**, 1100-1104 (2016).
- 25. A. A. Burkov, Anomalous Hall Effect in Weyl Metals. *Phys Rev Lett* **113**, 187202 (2014).
- 26. Y. P. Du, B. Wan, D. Wang, L. Sheng, C. G. Duan, X. G. Wan, Dirac and Weyl Semimetal in XYBi ($X = Ba$, Eu; $Y = Cu$, Ag and Au). *Sci Rep-Uk* 5, 14423 (2015).
- 27. Z. J. Wang, M. G. Vergniory, S. Kushwaha, M. Hirschberger, E. V. Chulkov, A. Ernst, N. P. Ong, R. J. Cava, B. A. Bernevig, Time-Reversal-Breaking Weyl Fermions in Magnetic Heusler Alloys. *Phys Rev Lett* **117**, 236401 (2016).
- 28. G. Hua, S. Nie, Z. Song, R. Yu, G. Xu, K. Yao, Dirac semimetal in type-IV magnetic space groups. *Phys Rev B* **98**, 201116 (2018).
- 29. M. C. Rahn, J. R. Soh, S. Francoual, L. S. I. Veiga, J. Strempfer, J. Mardegan, D. Y. Yan, Y. F. Guo, Y. G. Shi, A. T. Boothroyd, Coupling of magnetic order and charge transport in the candidate Dirac semimetal $\{\text{EuCd}\}_{2}\{\text{Amathrm}\{As\}\}_{2}\$. *Phys Rev B* **97**, 214422 (2018).
- 30. A. Artmann, A. Mewis, M. Roepke, G. Michels, AM(2)X(2) compounds with the CaAl2Si2-Type structure .11. Structure and properties of $ACd(2)X(2)$ (A: Eu, Yb; X: P, As, Sb). *Z Anorg Allg Chem* **622**, 679-682 (1996).
- 31. I. Schellenberg, U. Pfannenschmidt, M. Eul, C. Schwickert, R. Pottgen, A Sb-121 and Eu-151 Mossbauer Spectroscopic Investigation of EuCd2X2 ($X = P$, As, Sb) and YbCd2Sb2. *Z Anorg Allg Chem* **637**, 1863-1870 (2011).
- 32. H. P. Wang, D. S. Wu, Y. G. Shi, N. L. Wang, Anisotropic transport and optical spectroscopy study on antiferromagnetic triangular lattice EuCd2As2: An interplay between magnetism and charge transport properties. *Phys Rev B* **94**, 045112 (2016).
- 33. J. Krishna, T. Nautiyal, T. Maitra, First-principles study of electronic structure, transport, and optical properties of ${\mathcalEuCd}\$ $\{2}{\mathcalAs}\$ $\{2\$ *f. Phys Rev B* **98**, 125110 (2018).
- 34. P. Hohenberg, W. Kohn, Inhomogeneous Electron Gas. *Phys. Rev.* **136**, B864-B871 (1964).
- 35. W. Kohn, L. J. Sham, Self-Consistent Equations Including Exchange and Correlation Effects. *Phys. Rev.* **140**, A1133-A1138 (1965).
- 36. J. P. Perdew, K. Burke, M. Ernzerhof, Generalized gradient approximation made simple. *Phys Rev Lett* **77**, 3865-3868 (1996).
- 37. P. E. Blöchl, Projector Augmented-Wave Method. *Phys Rev B* **50**, 17953-17979 (1994).
- 38. G. Kresse, J. Furthmuller, Efficient Iterative Schemes for Ab initio Total-Energy Calculations Using a Plane-Wave Basis Set. *Phys Rev B* **54**, 11169-11186 (1996).
- 39. G. Kresse, J. Furthmuller, Efficiency of Ab-initio Total Energy Calculations for Metals and Semiconductors Using a Plane-Wave Basis Set. *Comp Mater Sci* **6**, 15-50 (1996).
- 40. N. Marzari, D. Vanderbilt, Maximally localized generalized Wannier functions for composite energy bands. *Phys Rev B* **56**, 12847-12865 (1997).
- 41. I. Souza, N. Marzari, D. Vanderbilt, Maximally localized Wannier functions for entangled energy bands. *Phys Rev B* **65**, 035109 (2001).
- 42. N. Marzari, A. A. Mostofi, J. R. Yates, I. Souza, D. Vanderbilt, Maximally localized Wannier functions: Theory and applications. *Rev Mod Phys* **84**, 1419-1475 (2012).
- 43. Q. Wu, S. Zhang, H.-F. Song, M. Troyer, A. A. Soluyanov, WannierTools: An opensource software package for novel topological materials. *Computer Physics Communications* **224**, 405-416 (2018).
- 44. D. H. Lee, J. D. Joannopoulos, Simple Scheme for Surface-Band Calculations .1. *Phys Rev B* **23**, 4988-4996 (1981).
- 45. D. H. Lee, J. D. Joannopoulos, Simple Scheme for Surface-Band Calculations .2. The Greens-Function. *Phys Rev B* **23**, 4997-5004 (1981).
- 46. M. P. L. Sancho, J. M. L. Sancho, J. Rubio, Quick Iterative Scheme for the Calculation of Transfer-Matrices - Application to Mo(100). *J Phys F Met Phys* **14**, 1205-1215 (1984).
- 47. M. P. L. Sancho, J. M. L. Sancho, J. Rubio, Highly Convergent Schemes for the Calculation of Bulk and Surface Green-Functions. *J Phys F Met Phys* **15**, 851-858 (1985).
- 48. H. J. Monkhorst, J. D. Pack, Special Points for Brillouin-Zone Integrations. *Phys Rev B* **13**, 5188-5192 (1976).
- 49. B. J. Yang, N. Nagaosa, Classification of stable three-dimensional Dirac semimetals with nontrivial topology. *Nat Commun* **5**, 4898 (2014).
- 50. Z. J. Wang, Y. Sun, X. Q. Chen, C. Franchini, G. Xu, H. M. Weng, X. Dai, Z. Fang, Dirac semimetal and topological phase transitions in A(3)Bi (A = Na, K, Rb). *Phys Rev B* **85**, 195320 (2012).
- 51. Z. J. Wang, H. M. Weng, Q. S. Wu, X. Dai, Z. Fang, Three-dimensional Dirac semimetal and quantum transport in Cd3As2. *Phys Rev B* **88**, 125427 (2013).
- 52. J. R. Soh, F. de Juan, M. G. Vergniory, N. B. M. Schröter, M. C. Rahn, D. Y. Yan, M. Bristow, P. A. Reiss, J. N. Blandy, Y. F. Guo, Y. G. Shi, T. K. Kim, A. McCollam, S. H. Simon, Y. Chen, A. I. Coldea, A. T. Boothroyd, An ideal Weyl semimetal induced by magnetic exchange. *arXiv:1901.10022*, (2019).